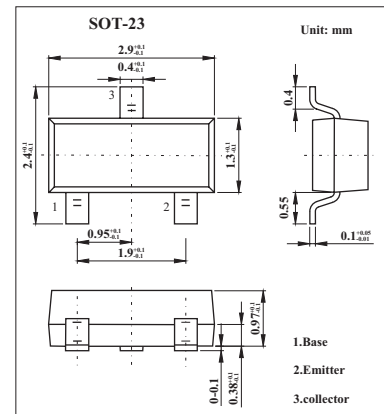


High Voltage Transistor

FMMT596

■ Features

- SOT23 PNP silicon planar

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-220	V
Collector-emitter voltage	V_{CE0}	-200	V
Emitter-base voltage	V_{EB0}	-5	V
Peak collector current	I_{CM}	-1	A
Collector current	I_C	-0.3	A
Base current	I_B	-200	mA
Power dissipation	P_{tot}	500	mW
Operating and storage temperature range	T_j, T_{stg}	-55 to +150	$^\circ\text{C}$

FMMT596■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}$	-220			V
Collector-emitter breakdown voltage *	$V_{(BR)CEO}$	$I_C = -10\text{mA}$	-200			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}$	-5			V
Collector cutoff current	I_{CBO}	$V_{CB} = -200\text{V}$			-100	nA
Collector-Emitter Cut-Off Current	I_{CES}	$V_{CE} = -200\text{V}$			-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4\text{V}$			-100	nA
Collector-emitter saturation voltage *	$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$			-0.2	V
		$I_C = -250\text{mA}, I_B = -25\text{mA}$			-0.35	V
Base-emitter saturation voltage *	$V_{BE(sat)}$	$I_C = -250\text{mA}, I_B = -25\text{mA}$			-1.0	V
Base-emitter voltage *	$V_{BE(ON)}$	$I_C = -250\text{mA}, V_{CE} = -10\text{V}$			-0.9	V
Static Forward Current Transfer Ratio	h_{FE}	$I_C = -1\text{mA}, V_{CE} = -10\text{V}$	100			
		$I_C = -100\text{mA}, V_{CE} = -10\text{V}^*$	100			
		$I_C = -250\text{mA}, V_{CE} = -10\text{V}^*$	85		300	
		$I_C = -400\text{mA}, V_{CE} = -10\text{V}^*$	35			
Current-gain-bandwidth product	f_T	$I_C = -50\text{mA}, V_{CE} = -10\text{V}, f = 100\text{MHz}$	150			MHz
Output capacitance	C_{obo}	$V_{CB} = -10\text{V}, f = 1\text{MHz}$			10	pF

* Pulse test: $t_p = 300\mu\text{s}$; $d \leq 0.02$.

■ Marking

Marking	596
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